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Understanding Embedded - FPGAs (Field Programmable Gate Array)

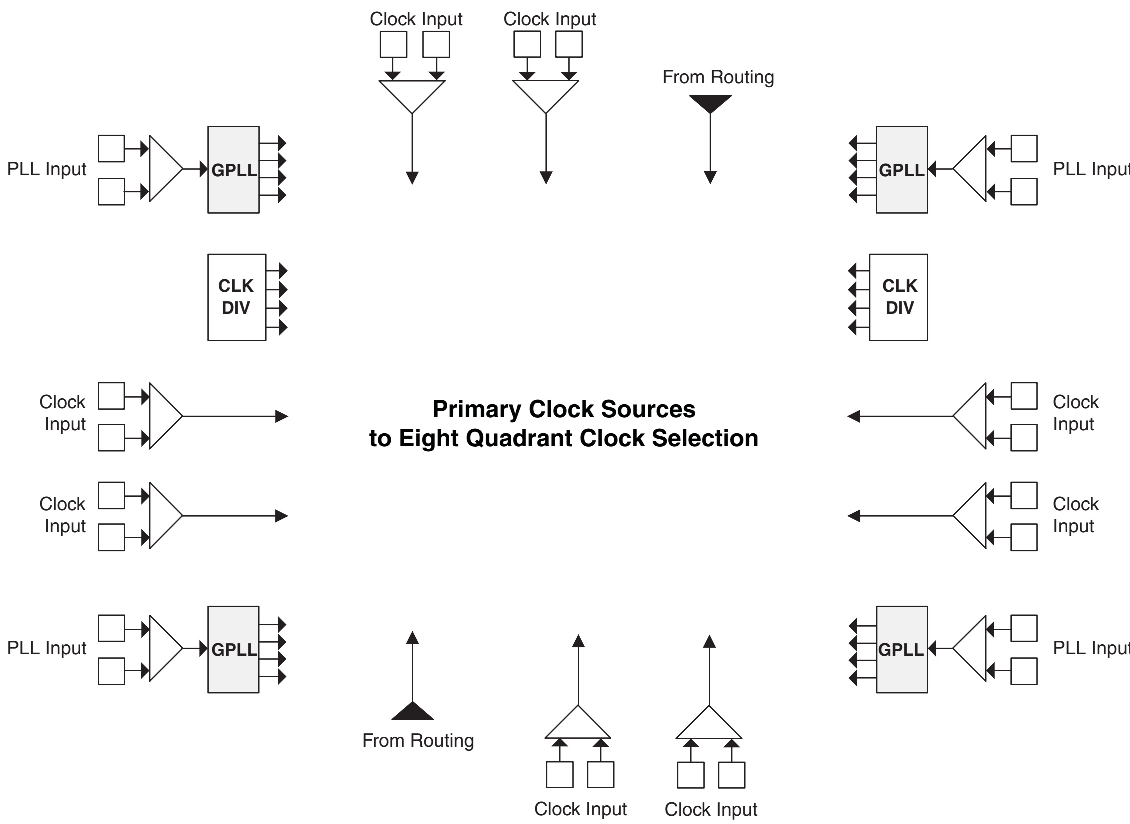
Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

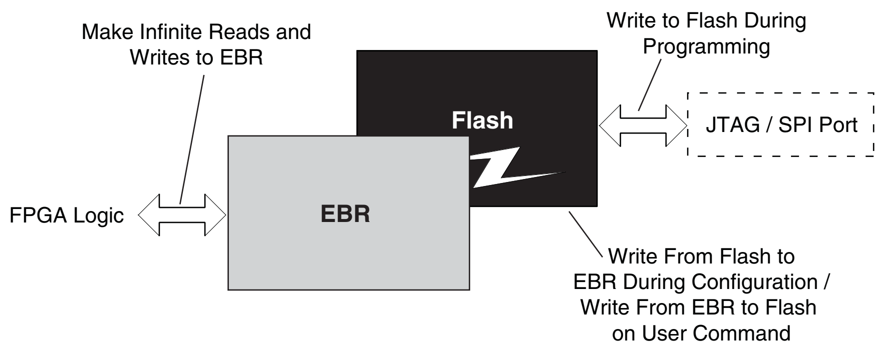
Details	
Product Status	Obsolete
Number of LABs/CLBs	5000
Number of Logic Elements/Cells	40000
Total RAM Bits	906240
Number of I/O	363
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	484-BBGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfxp2-40e-7f484c

Figure 2-6. Primary Clock Sources for XP2-17



Note: This diagram shows sources for the XP2-17 device. Smaller LatticeXP2 devices have two GPLLs.

Figure 2-16. FlashBAK Technology



Memory Cascading

Larger and deeper blocks of RAMs can be created using EBR sysMEM Blocks. Typically, the Lattice design tools cascade memory transparently, based on specific design inputs.

Single, Dual and Pseudo-Dual Port Modes

In all the sysMEM RAM modes the input data and address for the ports are registered at the input of the memory array. The output data of the memory is optionally registered at the output.

EBR memory supports two forms of write behavior for single port or dual port operation:

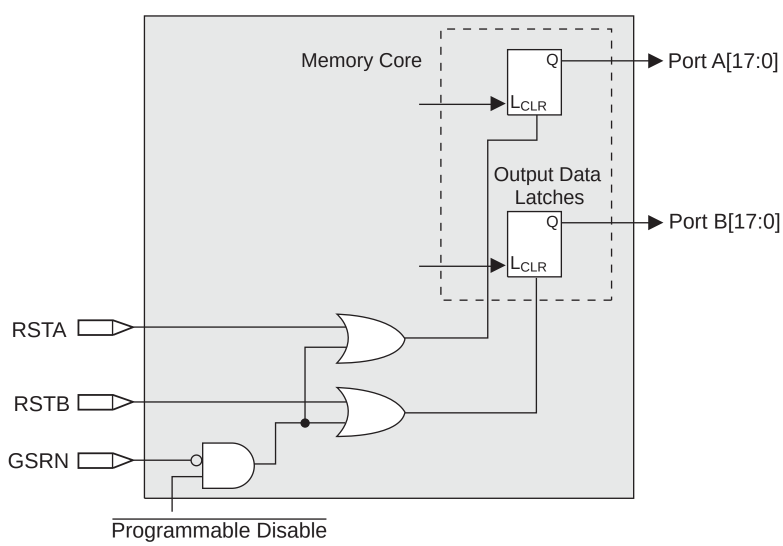
1. Normal – Data on the output appears only during a read cycle. During a write cycle, the data (at the current address) does not appear on the output. This mode is supported for all data widths.

2. Write Through – A copy of the input data appears at the output of the same port during a write cycle. This mode is supported for all data widths.

Memory Core Reset

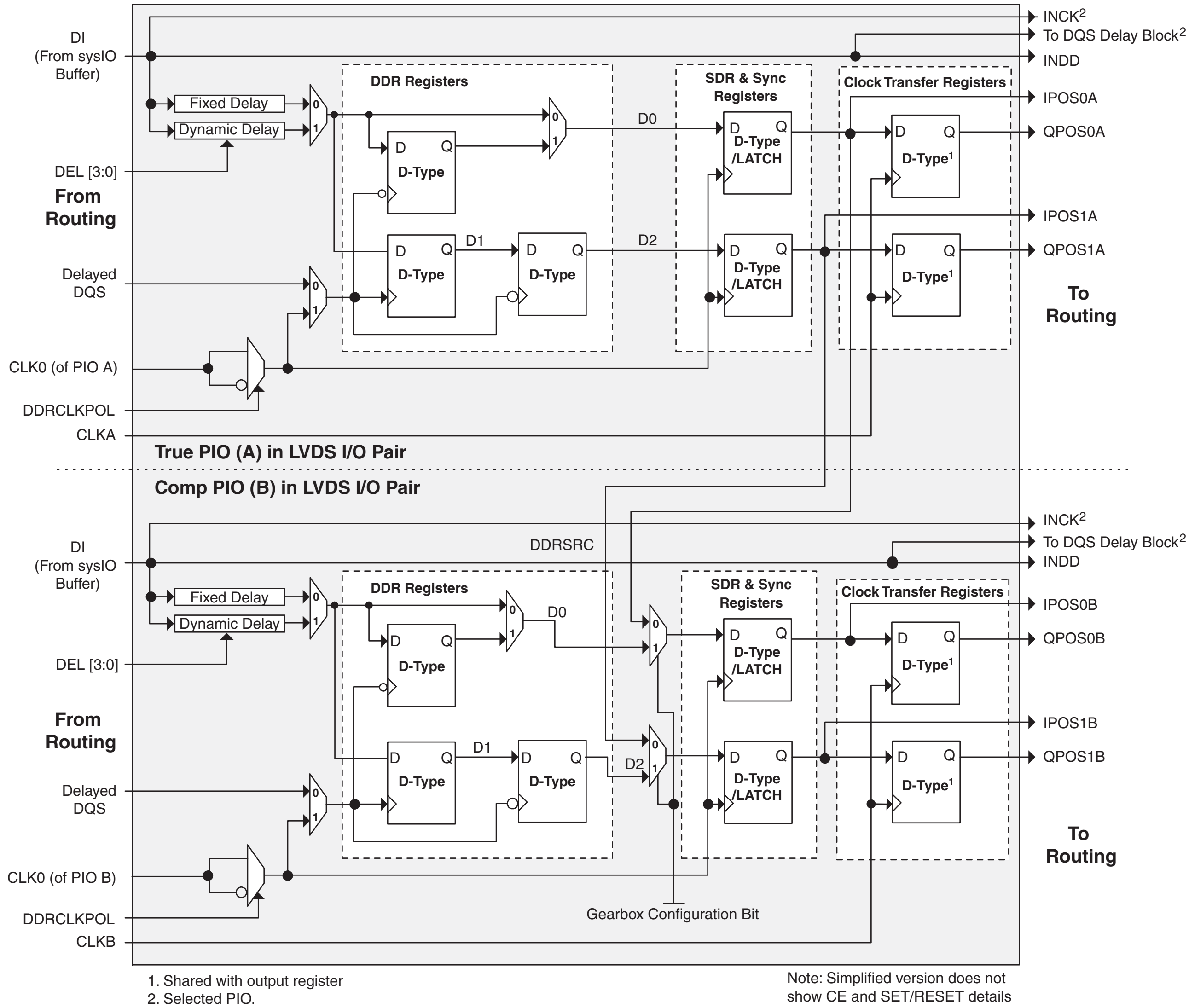
The memory array in the EBR utilizes latches at the A and B output ports. These latches can be reset asynchronously or synchronously. RSTA and RSTB are local signals, which reset the output latches associated with Port A and Port B respectively. GSRN, the global reset signal, resets both ports. The output data latches and associated resets for both ports are as shown in Figure 2-17.

Figure 2-17. Memory Core Reset



The signal DDRCLKPOL controls the polarity of the clock used in the synchronization registers. It ensures adequate timing when data is transferred from the DQS to system clock domain. For further discussion on this topic, see the DDR Memory section of this data sheet.

Figure 2-26. Input Register Block



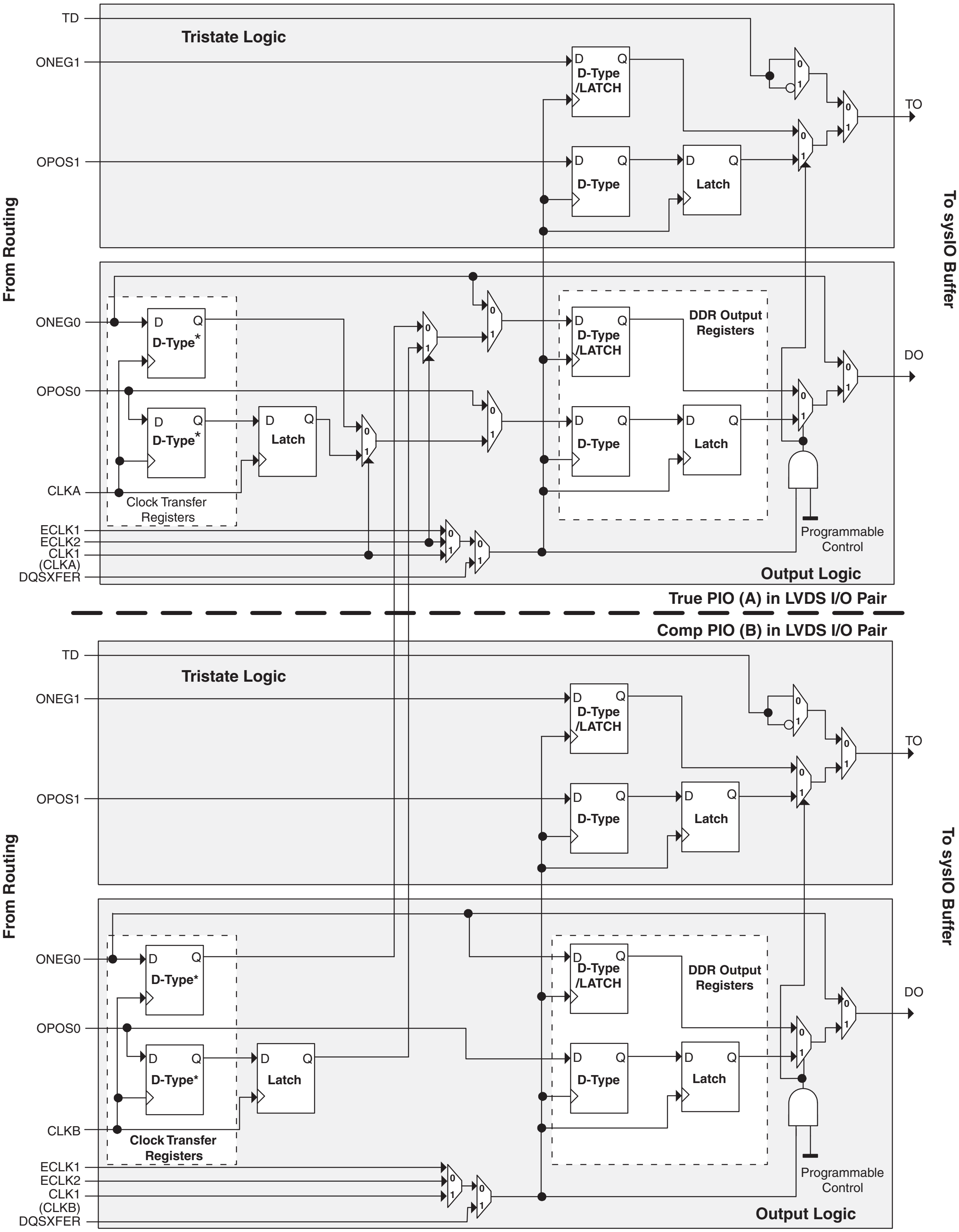
Output Register Block

The output register block provides the ability to register signals from the core of the device before they are passed to the sysIO buffers. The blocks on the PIOs on the left, right and bottom contain registers for SDR operation that are combined with an additional latch for DDR operation. Figure 2-27 shows the diagram of the Output Register Block for PIOs.

In SDR mode, ONEG0 feeds one of the flip-flops that then feeds the output. The flip-flop can be configured as a D-type or latch. In DDR mode, ONEG0 and OPOS0 are fed into registers on the positive edge of the clock. At the next clock cycle the registered OPOS0 is latched. A multiplexer running off the same clock cycle selects the correct register to feed the output (D0).

By combining output blocks of the complementary PIOs and sharing some registers from input blocks, a gearbox function can be implemented, to take four data streams ONEG0A, ONEG1A, ONEG1B and ONEG1B. Figure 2-27 shows the diagram using this gearbox function. For more information on this topic, see TN1138, LatticeXP2 High Speed I/O Interface.

Figure 2-27. Output and Tristate Block



* Shared with input register

Note: Simplified version does not show CE and SET/RESET details

Tristate Register Block

The tristate register block provides the ability to register tri-state control signals from the core of the device before they are passed to the sysIO buffers. The block contains a register for SDR operation and an additional latch for DDR operation. Figure 2-27 shows the Tristate Register Block with the Output Block

In SDR mode, ONEG1 feeds one of the flip-flops that then feeds the output. The flip-flop can be configured as D-type or latch. In DDR mode, ONEG1 and OPOS1 are fed into registers on the positive edge of the clock. Then in the next clock the registered OPOS1 is latched. A multiplexer running off the same clock cycle selects the correct register for feeding to the output (D0).

Control Logic Block

The control logic block allows the selection and modification of control signals for use in the PIO block. A clock signal is selected from general purpose routing, ECLK1, ECLK2 or a DQS signal (from the programmable DQS pin) and is provided to the input register block. The clock can optionally be inverted.

DDR Memory Support

PICs have additional circuitry to allow implementation of high speed source synchronous and DDR memory interfaces.

PICs have registered elements that support DDR memory interfaces. Interfaces on the left and right edges are designed for DDR memories that support 16 bits of data, whereas interfaces on the top and bottom are designed for memories that support 18 bits of data. One of every 16 PIOs on the left and right and one of every 18 PIOs on the top and bottom contain delay elements to facilitate the generation of DQS signals. The DQS signals feed the DQS buses which span the set of 16 or 18 PIOs. Figure 2-28 and Figure 2-29 show the DQS pin assignments in each set of PIOs.

The exact DQS pins are shown in a dual function in the Logic Signal Connections table in this data sheet. Additional detail is provided in the Signal Descriptions table. The DQS signal from the bus is used to strobe the DDR data from the memory into input register blocks. For additional information on using DDR memory support please see TN1138, LatticeXP2 High Speed I/O Interface.

DLL Calibrated DQS Delay Block

Source synchronous interfaces generally require the input clock to be adjusted in order to correctly capture data at the input register. For most interfaces a PLL is used for this adjustment. However, in DDR memories the clock, referred to as DQS, is not free-running, and this approach cannot be used. The DQS Delay block provides the required clock alignment for DDR memory interfaces.

The DQS signal (selected PIOs only, as shown in Figure 2-30) feeds from the PAD through a DQS delay element to a dedicated DQS routing resource. The DQS signal also feeds polarity control logic which controls the polarity of the clock to the sync registers in the input register blocks. Figure 2-30 and Figure 2-31 show how the DQS transition signals are routed to the PIOs.

The temperature, voltage and process variations of the DQS delay block are compensated by a set of 6-bit bus calibration signals from two dedicated DLLs (DDR_DLL) on opposite sides of the device. Each DLL compensates DQS delays in its half of the device as shown in Figure 2-30. The DLL loop is compensated for temperature, voltage and process variations by the system clock and feedback loop.

Figure 2-30. Edge Clock, DLL Calibration and DQS Local Bus Distribution

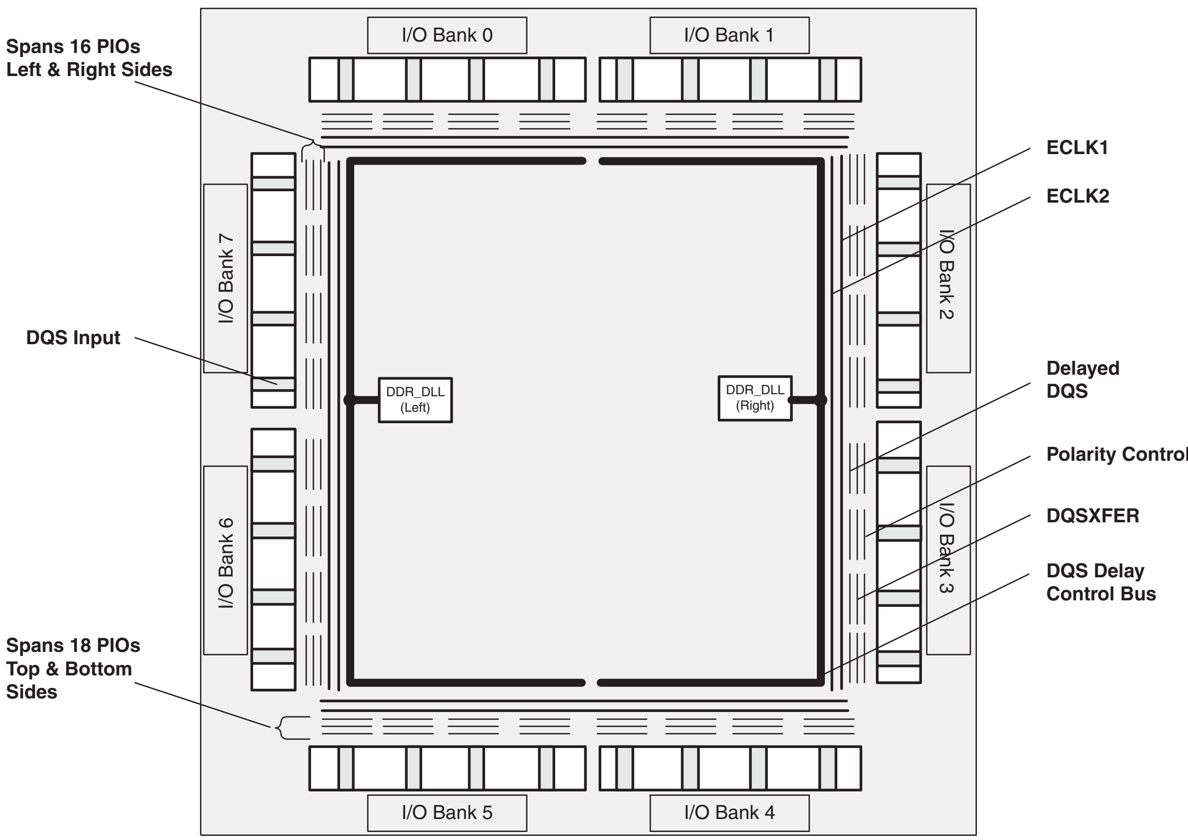
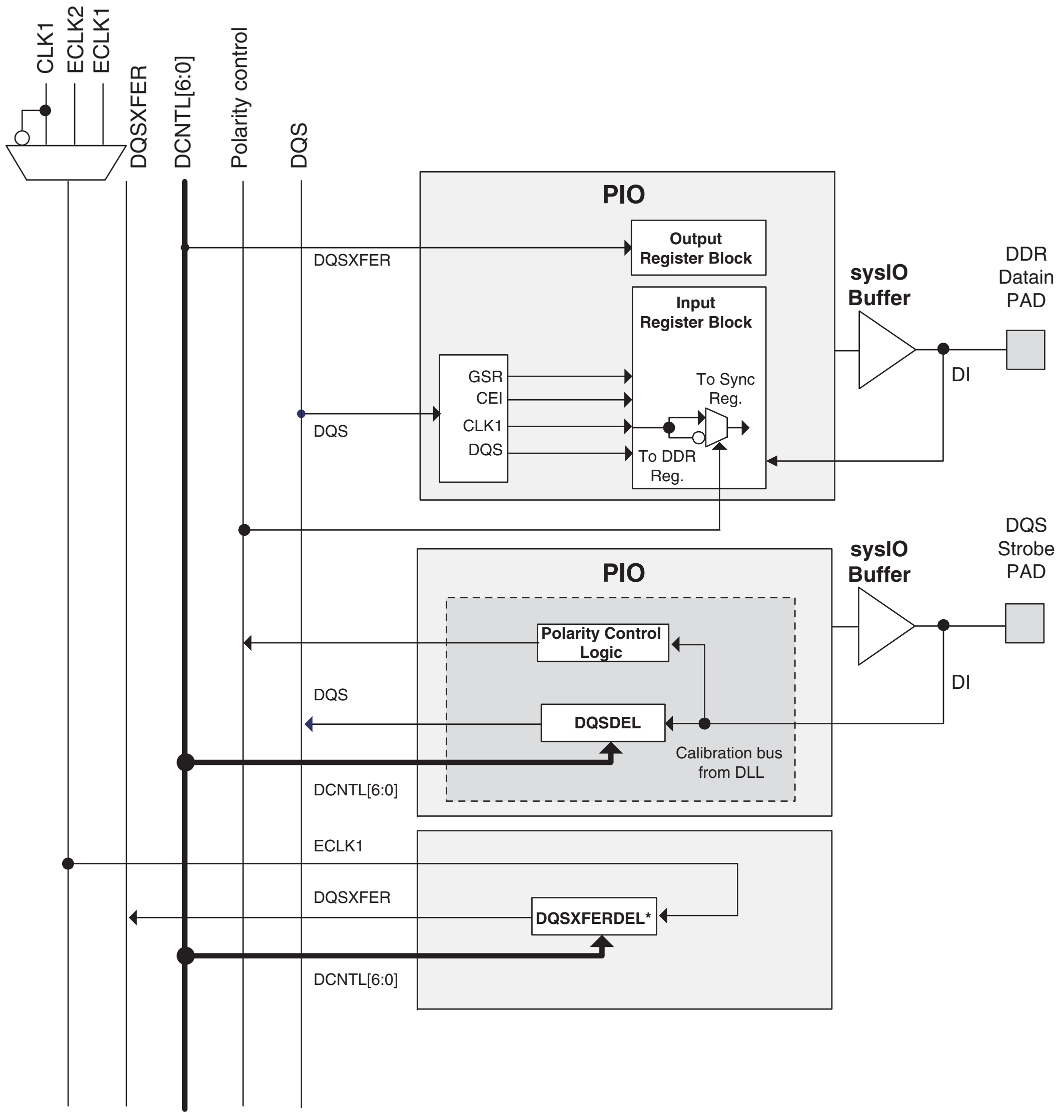


Figure 2-31. DQS Local Bus



*DQSXFERDEL shifts ECLK1 by 90% and is not associated with a particular PIO.

Polarity Control Logic

In a typical DDR memory interface design, the phase relationship between the incoming delayed DQS strobe and the internal system clock (during the READ cycle) is unknown. The LatticeXP2 family contains dedicated circuits to transfer data between these domains. To prevent set-up and hold violations, at the domain transfer between DQS (delayed) and the system clock, a clock polarity selector is used. This changes the edge on which the data is registered in the synchronizing registers in the input register block and requires evaluation at the start of each READ cycle for the correct clock polarity.

Prior to the READ operation in DDR memories, DQS is in tristate (pulled by termination). The DDR memory device drives DQS low at the start of the preamble state. A dedicated circuit detects this transition. This signal is used to control the polarity of the clock to the synchronizing registers.

DQSXFER

LatticeXP2 devices provide a DQSXFER signal to the output buffer to assist it in data transfer to DDR memories that require DQS strobe be shifted 90°. This shifted DQS strobe is generated by the DQSDEL block. The DQSXFER signal runs the span of the data bus.

sysIO Buffer

Each I/O is associated with a flexible buffer referred to as a sysIO buffer. These buffers are arranged around the periphery of the device in groups referred to as banks. The sysIO buffers allow users to implement the wide variety of standards that are found in today's systems including LVCMOS, SSTL, HSTL, LVDS and LVPECL.

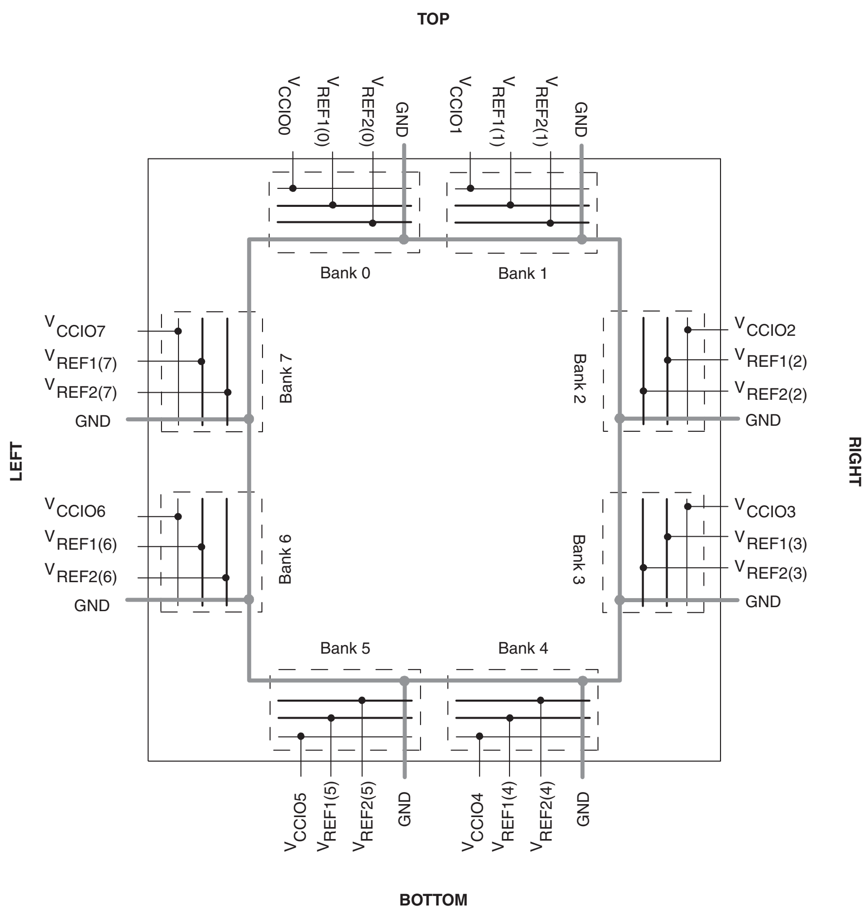
sysIO Buffer Banks

LatticeXP2 devices have eight sysIO buffer banks for user I/Os arranged two per side. Each bank is capable of supporting multiple I/O standards. Each sysIO bank has its own I/O supply voltage (V_{CCIO}). In addition, each bank has voltage references, V_{REF1} and V_{REF2}, that allow it to be completely independent from the others. Figure 2-32 shows the eight banks and their associated supplies.

In LatticeXP2 devices, single-ended output buffers and ratioed input buffers (LVTTL, LVCMOS and PCI) are powered using V_{CCIO}. LVTTL, LVCMOS33, LVCMOS25 and LVCMOS12 can also be set as fixed threshold inputs independent of V_{CCIO}.

Each bank can support up to two separate V_{REF} voltages, V_{REF1} and V_{REF2}, that set the threshold for the referenced input buffers. Some dedicated I/O pins in a bank can be configured to be a reference voltage supply pin. Each I/O is individually configurable based on the bank's supply and reference voltages.

Figure 2-32. LatticeXP2 Banks



LatticeXP2 devices contain two types of sysIO buffer pairs.

1. **Top and Bottom (Banks 0, 1, 4 and 5) sysIO Buffer Pairs (Single-Ended Outputs Only)**
   The sysIO buffer pairs in the top banks of the device consist of two single-ended output drivers and two sets of single-ended input buffers (both ratioed and referenced). One of the referenced input buffers can also be configured as a differential input.

   The two pads in the pair are described as “true” and “comp”, where the true pad is associated with the positive side of the differential input buffer and the comp (complementary) pad is associated with the negative side of the differential input buffer.

   Only the I/Os on the top and bottom banks have programmable PCI clamps.

2. **Left and Right (Banks 2, 3, 6 and 7) sysIO Buffer Pairs (50% Differential and 100% Single-Ended Outputs)**
   The sysIO buffer pairs in the left and right banks of the device consist of two single-ended output drivers, two sets of single-ended input buffers (both ratioed and referenced) and one differential output driver. One of the referenced input buffers can also be configured as a differential input.

   The two pads in the pair are described as “true” and “comp”, where the true pad is associated with the positive side of the differential I/O, and the comp pad is associated with the negative side of the differential I/O.

   LVDS differential output drivers are available on 50% of the buffer pairs on the left and right banks.

Typical sysIO I/O Behavior During Power-up

The internal power-on-reset (POR) signal is deactivated when V_{CC}, $V_{CCCONFIG}$ (V_{CCIO7}) and V_{CCAUX} have reached satisfactory levels. After the POR signal is deactivated, the FPGA core logic becomes active. It is the user’s responsibility to ensure that all other V_{CCIO} banks are active with valid input logic levels to properly control the output logic states of all the I/O banks that are critical to the application. During power up and before the FPGA core logic becomes active, all user I/Os will be high-impedance with weak pull-up. Please refer to TN1136, LatticeXP2 sysIO Usage Guide for additional information.

The V_{CC} and V_{CCAUX} supply the power to the FPGA core fabric, whereas the V_{CCIO} supplies power to the I/O buffers. In order to simplify system design while providing consistent and predictable I/O behavior, it is recommended that the I/O buffers be powered-up prior to the FPGA core fabric. V_{CCIO} supplies should be powered-up before or together with the V_{CC} and V_{CCAUX} supplies.

Supported sysIO Standards

The LatticeXP2 sysIO buffer supports both single-ended and differential standards. Single-ended standards can be further subdivided into LVCMOS, LVTTL and other standards. The buffers support the LVTTL, LVCMOS 1.2V, 1.5V, 1.8V, 2.5V and 3.3V standards. In the LVCMOS and LVTTL modes, the buffer has individual configuration options for drive strength, bus maintenance (weak pull-up, weak pull-down, or a bus-keeper latch) and open drain. Other single-ended standards supported include SSTL and HSTL. Differential standards supported include LVDS, MLVDS, BLVDS, LVPECL, RSDS, differential SSTL and differential HSTL. Tables 2-12 and 2-13 show the I/O standards (together with their supply and reference voltages) supported by LatticeXP2 devices. For further information on utilizing the sysIO buffer to support a variety of standards please see TN1136, LatticeXP2 sysIO Usage Guide.

original backup configuration and try again. This all can be done without power cycling the system. For more information please see TN1220, LatticeXP2 Dual Boot Feature.

For more information on device configuration, please see TN1141, LatticeXP2 sysCONFIG Usage Guide.

Soft Error Detect (SED) Support

LatticeXP2 devices have dedicated logic to perform Cyclic Redundancy Code (CRC) checks. During configuration, the configuration data bitstream can be checked with the CRC logic block. In addition, LatticeXP2 devices can be programmed for checking soft errors in SRAM. SED can be run on a programmed device when the user logic is not active. In the event a soft error occurs, the device can be programmed to either reload from a known good boot image (from internal Flash or external SPI memory) or generate an error signal.

For further information on SED support, please see TN1130, LatticeXP2 Soft Error Detection (SED) Usage Guide.

On-Chip Oscillator

Every LatticeXP2 device has an internal CMOS oscillator that is used to derive a Master Clock (CCLK) for configuration. The oscillator and CCLK run continuously and are available to user logic after configuration is complete. The available CCLK frequencies are listed in Table 2-14. When a different CCLK frequency is selected during the design process, the following sequence takes place:

1. Device powers up with the default CCLK frequency.
2. During configuration, users select a different CCLK frequency.
3. CCLK frequency changes to the selected frequency after clock configuration bits are received.

This internal CMOS oscillator is available to the user by routing it as an input clock to the clock tree. For further information on the use of this oscillator for configuration or user mode, please see TN1141, LatticeXP2 sysCONFIG Usage Guide.

Table 2-14. Selectable CCLKs and Oscillator Frequencies During Configuration and User Mode

CCLK/Oscillator (MHz)
2.5[1]
3.1[2]
4.3
5.4
6.9
8.1
9.2
10
13
15
20
26
32
40
54
80[3]
163[3]

1. Software default oscillator frequency.
2. Software default CCLK frequency.
3. Frequency not valid for CCLK.

Table 3-1. LVDS25E DC Conditions

Parameter	Description	Typical	Units
V_{CCIO}	Output Driver Supply (+/-5%)	2.50	V
Z_{OUT}	Driver Impedance	20	Ω
R_S	Driver Series Resistor (+/-1%)	158	Ω
R_P	Driver Parallel Resistor (+/-1%)	140	Ω
R_T	Receiver Termination (+/-1%)	100	Ω
V_{OH}	Output High Voltage (after R_P)	1.43	V
V_{OL}	Output Low Voltage (after R_P)	1.07	V
V_{OD}	Output Differential Voltage (After R_P)	0.35	V
V_{CM}	Output Common Mode Voltage	1.25	V
Z_{BACK}	Back Impedance	100.5	Ω
I_{DC}	DC Output Current	6.03	mA

LVCMOS33D

All I/O banks support emulated differential I/O using the LVCMOS33D I/O type. This option, along with the external resistor network, provides the system designer the flexibility to place differential outputs on an I/O bank with 3.3V VCCIO. The default drive current for LVCMOS33D output is 12mA with the option to change the device strength to 4mA, 8mA, 16mA or 20mA. Follow the LVCMOS33 specifications for the DC characteristics of the LVCMOS33D.

RSDS

The LatticeXP2 devices support differential RSDS standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The RSDS input standard is supported by the LVDS differential input buffer. The scheme shown in Figure 3-4 is one possible solution for RSDS standard implementation. Resistor values in Figure 3-4 are industry standard values for 1% resistors.

Figure 3-4. RSDS (Reduced Swing Differential Standard)

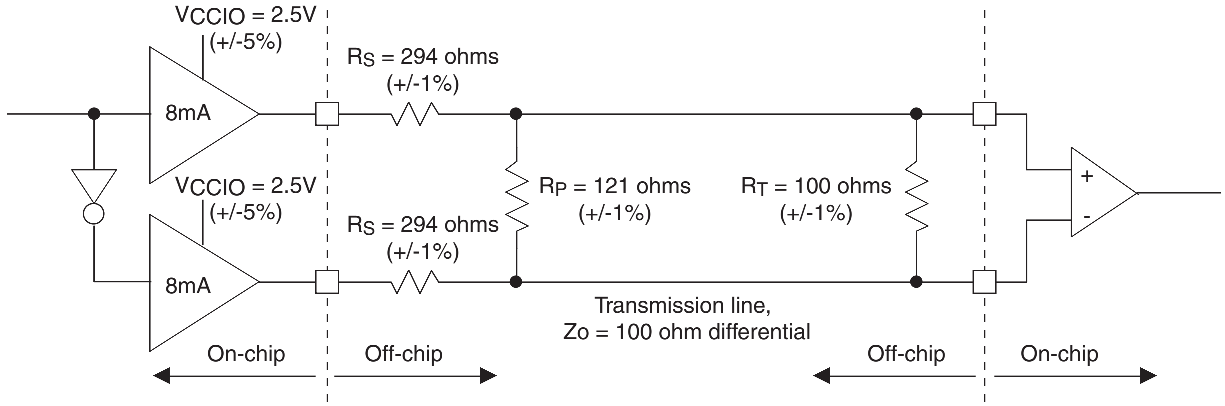


Table 3-4. RSDS DC Conditions[1]

Over Recommended Operating Conditions

Parameter	Description	Typical	Units
V_{CCIO}	Output Driver Supply (+/-5%)	2.50	V
Z_{OUT}	Driver Impedance	20	Ω
R_S	Driver Series Resistor (+/-1%)	294	Ω
R_P	Driver Parallel Resistor (+/-1%)	121	Ω
R_T	Receiver Termination (+/-1%)	100	Ω
V_{OH}	Output High Voltage (After R_P)	1.35	V
V_{OL}	Output Low Voltage (After R_P)	1.15	V
V_{OD}	Output Differential Voltage (After R_P)	0.20	V
V_{CM}	Output Common Mode Voltage	1.25	V
Z_{BACK}	Back Impedance	101.5	Ω
I_{DC}	DC Output Current	3.66	mA

1. For input buffer, see LVDS table.

Typical Building Block Function Performance[1]

Pin-to-Pin Performance (LVCMOS25 12mA Drive)

Function	-7 Timing	Units
Basic Functions		
16-bit Decoder	4.4	ns
32-bit Decoder	5.2	ns
64-bit Decoder	5.6	ns
4:1 MUX	3.7	ns
8:1 MUX	3.9	ns
16:1 MUX	4.3	ns
32:1 MUX	4.5	ns

Register-to-Register Performance

Function	-7 Timing	Units
Basic Functions		
16-bit Decoder	521	MHz
32-bit Decoder	537	MHz
64-bit Decoder	484	MHz
4:1 MUX	744	MHz
8:1 MUX	678	MHz
16:1 MUX	616	MHz
32:1 MUX	529	MHz
8-bit Adder	570	MHz
16-bit Adder	507	MHz
64-bit Adder	293	MHz
16-bit Counter	541	MHz
32-bit Counter	440	MHz
64-bit Counter	321	MHz
64-bit Accumulator	261	MHz
Embedded Memory Functions		
512x36 Single Port RAM, EBR Output Registers	315	MHz
1024x18 True-Dual Port RAM (Write Through or Normal, EBR Output Registers)	315	MHz
1024x18 True-Dual Port RAM (Write Through or Normal, PLC Output Registers)	231	MHz
Distributed Memory Functions		
16x4 Pseudo-Dual Port RAM (One PFU)	760	MHz
32x2 Pseudo-Dual Port RAM	455	MHz
64x1 Pseudo-Dual Port RAM	351	MHz
DSP Functions		
18x18 Multiplier (All Registers)	342	MHz
9x9 Multiplier (All Registers)	342	MHz
36x36 Multiply (All Registers)	330	MHz
18x18 Multiply/Accumulate (Input and Output Registers)	218	MHz
18x18 Multiply-Add/Sub-Sum (All Registers)	292	MHz

LatticeXP2 External Switching Characteristics (Continued)

Over Recommended Operating Conditions

Parameter	Description	Device	-7		-6		-5		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
t_{HE}	Clock to Data Hold - PIO Input Register	XP2-5	1.00	—	1.30	—	1.60	—	ns
		XP2-8	1.00	—	1.30	—	1.60	—	ns
		XP2-17	1.00	—	1.30	—	1.60	—	ns
		XP2-30	1.20	—	1.60	—	1.90	—	ns
		XP2-40	1.20	—	1.60	—	1.90	—	ns
t_{SU_DELE}	Clock to Data Setup - PIO Input Register with Data Input Delay	XP2-5	1.00	—	1.30	—	1.60	—	ns
		XP2-8	1.00	—	1.30	—	1.60	—	ns
		XP2-17	1.00	—	1.30	—	1.60	—	ns
		XP2-30	1.20	—	1.60	—	1.90	—	ns
		XP2-40	1.20	—	1.60	—	1.90	—	ns
t_{H_DELE}	Clock to Data Hold - PIO Input Register with Input Data Delay	XP2-5	0.00	—	0.00	—	0.00	—	ns
		XP2-8	0.00	—	0.00	—	0.00	—	ns
		XP2-17	0.00	—	0.00	—	0.00	—	ns
		XP2-30	0.00	—	0.00	—	0.00	—	ns
		XP2-40	0.00	—	0.00	—	0.00	—	ns
f_{MAX_IOE}	Clock Frequency of I/O and PFU Register	XP2	—	420	—	357	—	311	MHz
General I/O Pin Parameters (using Primary Clock with PLL)[1]									
t_{COPLL}	Clock to Output - PIO Output Register	XP2-5	—	3.00	—	3.30	—	3.70	ns
		XP2-8	—	3.00	—	3.30	—	3.70	ns
		XP2-17	—	3.00	—	3.30	—	3.70	ns
		XP2-30	—	3.00	—	3.30	—	3.70	ns
		XP2-40	—	3.00	—	3.30	—	3.70	ns
t_{SUPLL}	Clock to Data Setup - PIO Input Register	XP2-5	1.00	—	1.20	—	1.40	—	ns
		XP2-8	1.00	—	1.20	—	1.40	—	ns
		XP2-17	1.00	—	1.20	—	1.40	—	ns
		XP2-30	1.00	—	1.20	—	1.40	—	ns
		XP2-40	1.00	—	1.20	—	1.40	—	ns
t_{HPLL}	Clock to Data Hold - PIO Input Register	XP2-5	0.90	—	1.10	—	1.30	—	ns
		XP2-8	0.90	—	1.10	—	1.30	—	ns
		XP2-17	0.90	—	1.10	—	1.30	—	ns
		XP2-30	1.00	—	1.20	—	1.40	—	ns
		XP2-40	1.00	—	1.20	—	1.40	—	ns
t_{SU_DELPLL}	Clock to Data Setup - PIO Input Register with Data Input Delay	XP2-5	1.90	—	2.10	—	2.30	—	ns
		XP2-8	1.90	—	2.10	—	2.30	—	ns
		XP2-17	1.90	—	2.10	—	2.30	—	ns
		XP2-30	2.00	—	2.20	—	2.40	—	ns
		XP2-40	2.00	—	2.20	—	2.40	—	ns

LatticeXP2 Internal Switching Characteristics[1]

Over Recommended Operating Conditions

Parameter	Description	-7		-6		-5		Units
		Min.	Max.	Min.	Max.	Min.	Max.	
PFU/PFF Logic Mode Timing								
t_{LUT4_PFU}	LUT4 delay (A to D inputs to F output)	—	0.216	—	0.238	—	0.260	ns
t_{LUT6_PFU}	LUT6 delay (A to D inputs to OFX output)	—	0.304	—	0.399	—	0.494	ns
t_{LSR_PFU}	Set/Reset to output of PFU (Asynchronous)	—	0.720	—	0.769	—	0.818	ns
t_{SUM_PFU}	Clock to Mux (M0,M1) Input Setup Time	0.154	—	0.151	—	0.148	—	ns
t_{HM_PFU}	Clock to Mux (M0,M1) Input Hold Time	-0.061	—	-0.057	—	-0.053	—	ns
t_{SUD_PFU}	Clock to D input setup time	0.061	—	0.077	—	0.093	—	ns
t_{HD_PFU}	Clock to D input hold time	0.002	—	0.003	—	0.003	—	ns
t_{CK2Q_PFU}	Clock to Q delay, (D-type Register Configuration)	—	0.342	—	0.363	—	0.383	ns
t_{RSTREC_PFU}	Asynchronous reset recovery time for PFU Logic	—	0.520	—	0.634	—	0.748	ns
t_{RST_PFU}	Asynchronous reset time for PFU Logic	—	0.720	—	0.769	—	0.818	ns
PFU Dual Port Memory Mode Timing								
t_{CORAM_PFU}	Clock to Output (F Port)	—	1.082	—	1.267	—	1.452	ns
t_{SUDATA_PFU}	Data Setup Time	-0.206	—	-0.240	—	-0.274	—	ns
t_{HDATA_PFU}	Data Hold Time	0.239	—	0.275	—	0.312	—	ns
t_{SUADDR_PFU}	Address Setup Time	-0.294	—	-0.333	—	-0.371	—	ns
t_{HADDR_PFU}	Address Hold Time	0.295	—	0.333	—	0.371	—	ns
t_{SUWREN_PFU}	Write/Read Enable Setup Time	-0.146	—	-0.169	—	-0.193	—	ns
t_{HWREN_PFU}	Write/Read Enable Hold Time	0.158	—	0.182	—	0.207	—	ns
PIO Input/Output Buffer Timing								
t_{IN_PIO}	Input Buffer Delay (LVCMOS25)	—	0.858	—	0.766	—	0.674	ns
t_{OUT_PIO}	Output Buffer Delay (LVCMOS25)	—	1.561	—	1.403	—	1.246	ns
IOLOGIC Input/Output Timing								
t_{SUI_PIO}	Input Register Setup Time (Data Before Clock)	0.583	—	0.893	—	1.201	—	ns
t_{HI_PIO}	Input Register Hold Time (Data after Clock)	0.062	—	0.322	—	0.482	—	ns
t_{COO_PIO}	Output Register Clock to Output Delay	—	0.608	—	0.661	—	0.715	ns
t_{SUCE_PIO}	Input Register Clock Enable Setup Time	0.032	—	0.037	—	0.041	—	ns
t_{HCE_PIO}	Input Register Clock Enable Hold Time	-0.022	—	-0.025	—	-0.028	—	ns
t_{SULSR_PIO}	Set/Reset Setup Time	0.184	—	0.201	—	0.217	—	ns
t_{HLSR_PIO}	Set/Reset Hold Time	-0.080	—	-0.086	—	-0.093	—	ns
t_{RSTREC_PIO}	Asynchronous reset recovery time for IO Logic	0.228	—	0.247	—	0.266	—	ns

LatticeXP2 Internal Switching Characteristics[1] (Continued)

Over Recommended Operating Conditions

Parameter	Description	-7		-6		-5		Units
		Min.	Max.	Min.	Max.	Min.	Max.	
t_{RST_PIO}	Asynchronous reset time for PFU Logic	—	0.386	—	0.419	—	0.452	ns
t_{DEL}	Dynamic Delay Step Size	0.035	0.035	0.035	0.035	0.035	0.035	ns
EBR Timing								
t_{CO_EBR}	Clock (Read) to Output from Address or Data	—	2.774	—	3.142	—	3.510	ns
t_{COO_EBR}	Clock (Write) to Output from EBR Output Register	—	0.360	—	0.408	—	0.456	ns
t_{SUDATA_EBR}	Setup Data to EBR Memory (Write Clk)	-0.167	—	-0.198	—	-0.229	—	ns
t_{HDATA_EBR}	Hold Data to EBR Memory (Write Clk)	0.194	—	0.231	—	0.267	—	ns
t_{SUADDR_EBR}	Setup Address to EBR Memory (Write Clk)	-0.117	—	-0.137	—	-0.157	—	ns
t_{HADDR_EBR}	Hold Address to EBR Memory (Write Clk)	0.157	—	0.182	—	0.207	—	ns
t_{SUWREN_EBR}	Setup Write/Read Enable to EBR Memory (Write/Read Clk)	-0.135	—	-0.159	—	-0.182	—	ns
t_{HWREN_EBR}	Hold Write/Read Enable to EBR Memory (Write/Read Clk)	0.158	—	0.186	—	0.214	—	ns
t_{SUCE_EBR}	Clock Enable Setup Time to EBR Output Register (Read Clk)	0.144	—	0.160	—	0.176	—	ns
t_{HCE_EBR}	Clock Enable Hold Time to EBR Output Register (Read Clk)	-0.097	—	-0.113	—	-0.129	—	ns
t_{RSTO_EBR}	Reset To Output Delay Time from EBR Output Register (Asynchronous)	—	1.156	—	1.341	—	1.526	ns
t_{SUBE_EBR}	Byte Enable Set-Up Time to EBR Output Register	-0.117	—	-0.137	—	-0.157	—	ns
t_{HBE_EBR}	Byte Enable Hold Time to EBR Output Register Dynamic Delay on Each PIO	0.157	—	0.182	—	0.207	—	ns
t_{RSTREC_EBR}	Asynchronous reset recovery time for EBR	0.233	—	0.291	—	0.347	—	ns
t_{RST_EBR}	Asynchronous reset time for EBR	—	1.156	—	1.341	—	1.526	ns
PLL Parameters								
$t_{RSTKREC\_PLL}$	After RSTK De-assert, Recovery Time Before Next Clock Edge Can Toggle K-divider Counter	1.000	—	1.000	—	1.000	—	ns
t_{RSTREC_PLL}	After RST De-assert, Recovery Time Before Next Clock Edge Can Toggle M-divider Counter (Applies to M-Divider Portion of RST Only[2])	1.000	—	1.000	—	1.000	—	ns
DSP Block Timing								
t_{SUI_DSP}	Input Register Setup Time	0.135	—	0.151	—	0.166	—	ns
t_{HI_DSP}	Input Register Hold Time	0.021	—	-0.006	—	-0.031	—	ns
t_{SUP_DSP}	Pipeline Register Setup Time	2.505	—	2.784	—	3.064	—	ns

sysCLOCK PLL Timing

Over Recommended Operating Conditions

Parameter	Description	Conditions	Min.	Typ.	Max.	Units
f_{IN}	Input Clock Frequency (CLKI, CLKFB)		10	—	435	MHz
f_{OUT}	Output Clock Frequency (CLKOP, CLKOS)		10	—	435	MHz
f_{OUT2}	K-Divider Output Frequency	CLKOK	0.078	—	217.5	MHz
		CLKOK2	3.3	—	145	MHz
f_{VCO}	PLL VCO Frequency		435	—	870	MHz
f_{PFD}	Phase Detector Input Frequency		10	—	435	MHz
AC Characteristics						
t_{DT}	Output Clock Duty Cycle	Default duty cycle selected [3]	45	50	55	%
t_{CPA}	Coarse Phase Adjust		-5	0	5	%
t_{PH}[4]	Output Phase Accuracy		-5	0	5	%
t_{OPJIT}[1]	Output Clock Period Jitter	f_{OUT} > 400 MHz	—	—	±50	ps
		100 MHz < f_{OUT} < 400 MHz	—	—	±125	ps
		f_{OUT} < 100 MHz	—	—	0.025	UIPP
t_{SK}	Input Clock to Output Clock Skew	N/M = integer	—	—	±240	ps
t_{OPW}	Output Clock Pulse Width	At 90% or 10%	1	—	—	ns
t_{LOCK}[2]	PLL Lock-in Time	25 to 435 MHz	—	—	50	µs
		10 to 25 MHz	—	—	100	µs
t_{IPJIT}	Input Clock Period Jitter		—	—	±200	ps
t_{FBKDLY}	External Feedback Delay		—	—	10	ns
t_{HI}	Input Clock High Time	90% to 90%	0.5	—	—	ns
t_{LO}	Input Clock Low Time	10% to 10%	0.5	—	—	ns
t_{RSTKW}	Reset Signal Pulse Width (RSTK)		10	—	—	ns
t_{RSTW}	Reset Signal Pulse Width (RST)		500	—	—	ns

1. Jitter sample is taken over 10,000 samples of the primary PLL output with clean reference clock.
2. Output clock is valid after t_{LOCK} for PLL reset and dynamic delay adjustment.
3. Using LVDS output buffers.
4. Relative to CLKOP.

LatticeXP2 Family Data Sheet
Pinout Information

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Signal Descriptions

Signal Name	I/O	Description
General Purpose		
P[Edge] [Row/Column Number*]_[A/B]	I/O	[Edge] indicates the edge of the device on which the pad is located. Valid edge designations are L (Left), B (Bottom), R (Right), T (Top). [Row/Column Number] indicates the PFU row or the column of the device on which the PIC exists. When Edge is T (Top) or B (Bottom), only need to specify Row Number. When Edge is L (Left) or R (Right), only need to specify Column Number. [A/B] indicates the PIO within the PIC to which the pad is connected. Some of these user-programmable pins are shared with special function pins. These pins, when not used as special purpose pins, can be programmed as I/Os for user logic. During configuration the user-programmable I/Os are tri-stated with an internal pull-up resistor enabled. If any pin is not used (or not bonded to a package pin), it is also tri-stated with an internal pull-up resistor enabled after configuration.
GSRN	I	Global RESET signal (active low). Any I/O pin can be GSRN.
NC	—	No connect.
GND	—	Ground. Dedicated pins.
V_{CC}	—	Power supply pins for core logic. Dedicated pins.
V_{CCAUX}	—	Auxiliary power supply pin. This dedicated pin powers all the differential and referenced input buffers.
V_{CCPLL}	—	PLL supply pins. csBGA, PQFP and TQFP packages only.
V_{CCIOx}	—	Dedicated power supply pins for I/O bank x.
V_{REF1_x}, V_{REF2_x}	—	Reference supply pins for I/O bank x. Pre-determined pins in each bank are assigned as V_{REF} inputs. When not used, they may be used as I/O pins.
PLL and Clock Functions (Used as user programmable I/O pins when not in use for PLL or clock pins)		
[LOC][num]_V_{CCPLL}	—	Power supply pin for PLL: LLC, LRC, URC, ULC, num = row from center.
[LOC][num]_GPLL[T, C]_IN_A	I	General Purpose PLL (GPLL) input pads: LLC, LRC, URC, ULC, num = row from center, T = true and C = complement, index A,B,C...at each side.
[LOC][num]_GPLL[T, C]_FB_A	I	Optional feedback GPLL input pads: LLC, LRC, URC, ULC, num = row from center, T = true and C = complement, index A,B,C...at each side.
PCLK[T, C]_[n:0]_[3:0]	I	Primary Clock pads, T = true and C = complement, n per side, indexed by bank and 0,1,2,3 within bank.
[LOC]DQS[num]	I	DQS input pads: T (Top), R (Right), B (Bottom), L (Left), DQS, num = ball function number. Any pad can be configured to be output.
Test and Programming (Dedicated Pins)		
TMS	I	Test Mode Select input, used to control the 1149.1 state machine. Pull-up is enabled during configuration.
TCK	I	Test Clock input pin, used to clock the 1149.1 state machine. No pull-up enabled.
TDI	I	Test Data in pin. Used to load data into device using 1149.1 state machine. After power-up, this TAP port can be activated for configuration by sending appropriate command. (Note: once a configuration port is selected it is locked. Another configuration port cannot be selected until the power-up sequence). Pull-up is enabled during configuration.

LatticeXP2 Family Data Sheet Supplemental Information

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For Further Information

A variety of technical notes for the LatticeXP2 FPGA family are available on the Lattice Semiconductor web site at www.latticesemi.com.

- TN1136, LatticeXP2 sysIO Usage Guide
- TN1137, LatticeXP2 Memory Usage Guide
- TN1138, LatticeXP2 High Speed I/O Interface
- TN1126, LatticeXP2 sysCLOCK PLL Design and Usage Guide
- TN1139, Power Estimation and Management for LatticeXP2 Devices
- TN1140, LatticeXP2 sysDSP Usage Guide
- TN1141, LatticeXP2 sysCONFIG Usage Guide
- TN1142, LatticeXP2 Configuration Encryption and Security Usage Guide
- TN1087, Minimizing System Interruption During Configuration Using TransFR Technology
- TN1220, LatticeXP2 Dual Boot Feature
- TN1130, LatticeXP2 Soft Error Detection (SED) Usage Guide
- TN1143, LatticeXP2 Hardware Checklist

For further information on interface standards refer to the following websites:

- JEDEC Standards (LVTTL, LVCMOS, SSTL, HSTL): www.jedec.org
- PCI: www.pcisig.com

Date	Version	Section	Change Summary
April 2008 (cont.)	01.4 (cont.)	DC and Switching Characteristics (cont.)	Updated Flash Download Time (From On-Chip Flash to SRAM) Table
			Updated Flash Program Time Table
			Updated Flash Erase Time Table
			Updated FlashBAK (from EBR to Flash) Table
			Updated Hot Socketing Specifications Table footnotes
		Pinout Information	Updated Signal Descriptions Table
June 2008	01.5	Architecture	Removed Read-Before-Write sysMEM EBR mode.
			Clarification of the operation of the secondary clock regions.
		DC and Switching Characteristics	Removed Read-Before-Write sysMEM EBR mode.
		Pinout Information	Updated DDR Banks Bonding Out per I/O Bank section of Pin Information Summary Table.
August 2008	01.6	—	Data sheet status changed from preliminary to final.
		Architecture	Clarification of the operation of the secondary clock regions.
		DC and Switching Characteristics	Removed “8W” specification from Hot Socketing Specifications table.
			Removed "8W" footnote from DC Electrical Characteristics table.
			Updated Register-to-Register Performance table.
		Ordering Information	Removed “8W” option from Part Number Description.
			Removed XP2-17 “8W” OPNs.
April 2011	01.7	DC and Switching Characteristics	Recommended Operating Conditions table, added footnote 5.
			On-Chip Flash Memory Specifications table, added footnote 1.
			BLVDS DC Conditions, corrected column title to be Z0 = 90 ohms.
			sysCONFIG Port Timing Specifications table, added footnote 1 for t_{DINIT}.
January 2012	01.8	Multiple	Added support for Lattice Diamond design software.
		Architecture	Corrected information regarding SED support.
		DC and Switching Characteristics	Added reference to ESD Performance Qualification Summary information.
May 2013	01.9	All	Updated document with new corporate logo.
		Architecture	Architecture Overview – Added information on the state of the register on power up and after configuration.
			Added information regarding SED support.
		DC and Switching Characteristics	Removed Input Clock Rise/Fall Time 1ns max from the sysCLOCK PLL Timing table.
		Ordering Information	Updated topside mark in Ordering Information diagram.
March 2014	02.0	Architecture	Updated Typical sysIO I/O Behavior During Power-up section. Added information on POR signal deactivation.
August 2014	02.1	Architecture	Updated Typical sysIO I/O Behavior During Power-up section. Described user I/Os during power up and before FPGA core logic is active.
September 2014	2.2	DC and Switching Characteristics	Updated Switching Test Conditions section. Re-linked missing figure.